BAV19 – BAV21 Taiwan Semiconductor

200mA, 120V - 250V Switching Diode

FEATURES

• Low power loss, high efficiency

MICONDUCTOR

- High surge current capability
- Hermetically sealed glass
- RoHS Compliant

TAIWAN

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- On-board DC/DC converter

MECHANICAL DATA

- Case: DO-35
- Terminal: Pure tin plated leads, solderable per J-STD-002
- Polarity: Indicated by cathode band
- Weight: 101.67mg (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
١ _F	200	mA		
V _{RRM}	120 - 250	V		
I _{FSM}	4	А		
V_F at I_F = 100mA	1	V		
T _{J MAX}	175	°C		
Package	DO-35			
Configuration	Single die			



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	BAV19	BAV20	BAV21	UNIT
Marking code on the device			BAV19	BAV20	BAV21	
Repetitive peak reverse voltage		V _{RRM}	120	200	250	V
Forward current		I _F	200			mA
Non-Repetitive square wave peak forward	t = 1s	1	1 4		А	
surge current	t = 1µs	I _{FSM}				А
Junction temperature range		TJ	-55 to +175			°C
Storage temperature range		T _{STG}	-55 to +175			°C

THERMAL PERFORMANCE						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-ambient thermal resistance	R _{eja}	300	°C/W			



BAV19 – BAV21 Taiwan Semiconductor

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward voltage ⁽¹⁾		$I_F = 100 \text{mA}, T_J = 25^{\circ}\text{C}$	V _F	-	1.00	V
		$I_F = 200 \text{mA}, T_J = 25^{\circ}\text{C}$		-	1.25	V
	BAV19	V _R = 100 V	I _R	-	100	nA
	BAV20	V _R = 150 V		-	100	nA
	BAV21	V _R = 200 V		-	100	nA
Junction capacitance		$1MHz, V_R = 0V$	CJ	-	5	pF

Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION				
ORDERING CODE ⁽¹⁾	PACKAGE	PACKING		
BAVx R0G	DO-35	10,000 / 14" Reel		
BAVx A0G	DO-35	5,000 / Ammo Box		

Notes:

1. "x" defines voltage from 120V (BAV19) to 250V (BAV21)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$





Fig.3 Admissible Power Dissipation Curve



Fig.4 Typical Junction Capacitance





Taiwan Semiconductor

PACKAGE OUTLINE DIMENSIONS





Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies.

Purchasers are solely responsible for the choice, selection, and use of TSC products and TSC assumes no liability for application assistance or the design of Purchasers' products.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.